

Technical Data Data Sheet N1794, Rev. B **Green Products**

GBJ15005-GBJ1510

Single-Phase 15.0A Glass Passivated Bridge Rectifier

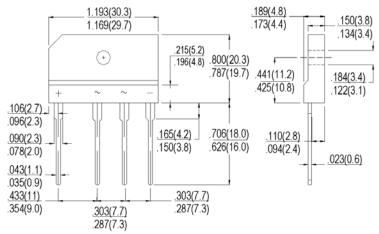
Features:

- Glass passivated die construction
- Low forward voltage drop
- High current capability
- High surge current capability
- Plastic material-UL flammability 94V-0

Mechanical Data:

- Case: GBJ, Molded plastic
- Terminals: Plated leads solderable per MIL-STD-202, Method 208
- Polarity: as marked on case
- Mounting Position: Any
- Weight: 0.23ounce, 6.6gram
- Mounting: Through Hole for #6 Screw
- Mounting Torque: 0.5 N.m Typical and 0.8 N.m Maximum

Mechanical Dimensions: In Inches/mm



GBJ

MARKING, MOLDING RESIN

Marking for Type Number, 1st row SSG YYWWL, 2nd row Type Number Where YY is the manufacture year WW is the manufacture week code L is the wafer's Lot Number

Ordering Information

Device	Package	Shipping
GBJ15005 THRU GBJ1510	GBJ (Pb-Free)	250pcs / Box

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

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Maximum Ratings and Electrical Characteristics Rating at 25°C ambient temperature unless otherwise specified. Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%

Maximum Ratings:

Type number	Symbol	GBJ 15005	GBJ 1501	GBJ 1502	GBJ 1504	GBJ 1506	GBJ 1508	GBJ 1510	Unit
Maximum Recurrent Peak Reverse Voltage Maximum DC Blocking Voltage	$V_{\text{RRM}} \ V_{\text{DC}}$	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum Average Forward Rectified Current with Heatsink at T_c =100 $^{\circ}$	I _(AV)	15.0							Α
Peak Forward Surge Current,8.3ms single half-sine-wave superimposed on rated load (JEDEC method)	I _{FSM}	200							Α

Electrical Characteristics:

Type Number	Symbol	GBJ 15005	GBJ 1501	GBJ 1502	GBJ 1504	GBJ 1506	GBJ 1508	GBJ 1510	Unit
Maximum Forward Voltage (per element) @I _F =7.5A	V_{F}	1.1							V
Maximum Reverse Current $@T_A=25^{\circ}C$ At Rated DC Blocking Voltage $@T_A=125^{\circ}C$	I _R	10 500						μA	
Typical Junction Capacitance (Note 1)	CJ	60						pF	

Thermal-Mechanical Specifications:

Type Number	Symbol	GBJ 15005	GBJ 1501	GBJ 1502	GBJ 1504	GBJ 1506	GBJ 1508	GBJ 1510	Unit
Typical Thermal Resistance (Note 2)	$R_{ heta JC}$	0.8							°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150							°C
Case Style	GBJ								

Note: 1- Measured at 1 MHZ and applied reverse voltage of 4.0 VDC.

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²⁻ Thermal Resistance from Junction to Case with Device Mounted on 300mm x 300mm x 1.6mmC u Plate Heatsink.

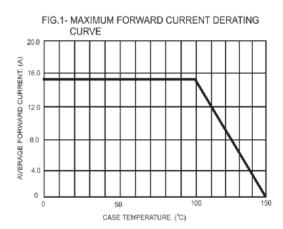
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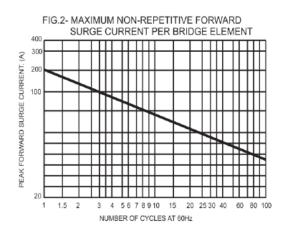


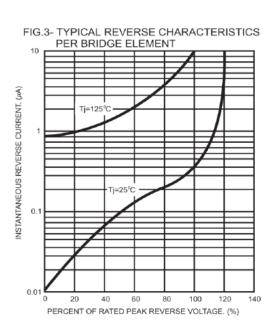
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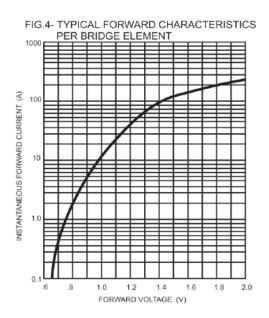
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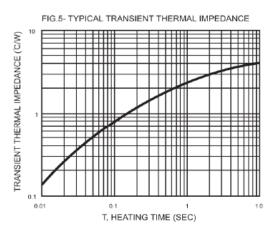
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